

3A 60V(1.37mm)

**Chip Information**

Chip Size	1.37 x 1.37mm
Pad Size	1.21 x 1.21mm
Chip Quantity	5772 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al-Ni-Au (For Solder)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	60	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	3	A	
Peak Forward Surge Current	IFSM	80	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.670		0.600	V	IF=3A Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.3	0.2	0.01	mA	VR=62V Ta=25degC
	IR2	30		3	mA	VR=60V Ta=100deg
	IR3				mA	
	IR4				mA	
Reverse Breakdown Voltage	BV	62	66	80	V	IR=0.5mA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back metal
XMB702	250 +/- 20um	Ti-Ni-Au (For Solder)

Note:  
Designed For SR306,SB360